



STB30NF10 STP30NF10 STP30NF10FP

N-CHANNEL 100V - 0.038 Ω - 35A TO-220/TO-220FP/D²PAK
LOW GATE CHARGE STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB30NF10	100 V	<0.045 Ω	35 A
STP30NF10	100 V	<0.045 Ω	35 A
STP30NF10FP	100 V	<0.045 Ω	18 A

- TYPICAL R_{DS(on)} = 0.038 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- SURFACE-MOUNTING D²PAK (TO-263)
POWER PACKAGE IN TUBE (NO SUFFIX) OR
IN TAPE & REEL (SUFFIX "T4")

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

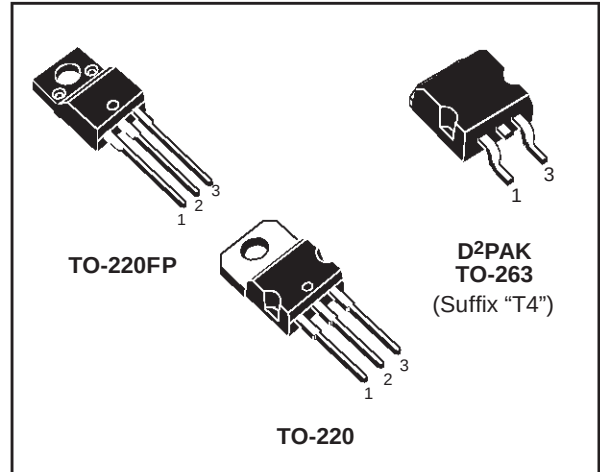
APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

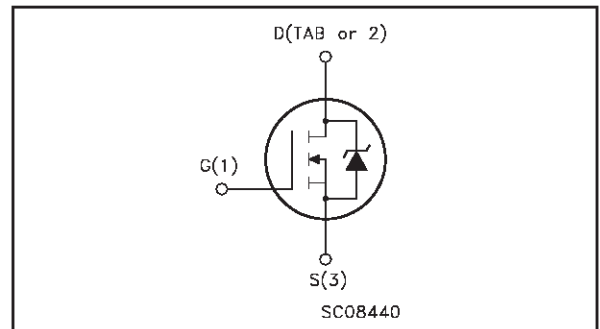
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STB30NF10 STP30NF10	STP30NF10FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	100		V
V _{GS}	Gate- source Voltage	± 20		V
I _D	Drain Current (continuous) at T _C = 25°C	35	18	A
I _D	Drain Current (continuous) at T _C = 100°C	25	13	A
I _{DM} (●)	Drain Current (pulsed)	140	72	A
P _{tot}	Total Dissipation at T _C = 25°C	115	30	W
	Derating Factor	0.77	0.2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	28		V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	275		mJ
V _{ISO}	Insulation Withstand Voltage (DC)	-----	2000	V
T _{stg}	Storage Temperature	-55 to 175		°C
T _j	Operating Junction Temperature			

(●) Pulse width limited by safe operating area.



INTERNAL SCHEMATIC DIAGRAM



(1) I_{SD} ≤ 30A, di/dt ≤ 400A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}
(2) Starting T_j = 25 °C, I_D = 15A, V_{DD} = 30V

STB30NF10 STP30NF10 STP30NF10FP**THERMAL DATA**

			D ² PAK TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case	Max	1.30	5	°C/W
R _{thj-amb} T _I	Thermal Resistance Junction-ambient Maximum Lead Temperature For Soldering Purpose	Max	62.5 300		°C/W °C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 15 A		0.038	0.045	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 15 A		10		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1180 180 80		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 15\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		15 40		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		40 8.0 15	55	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50\text{ V}$ $I_D = 15\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		45 10		ns ns

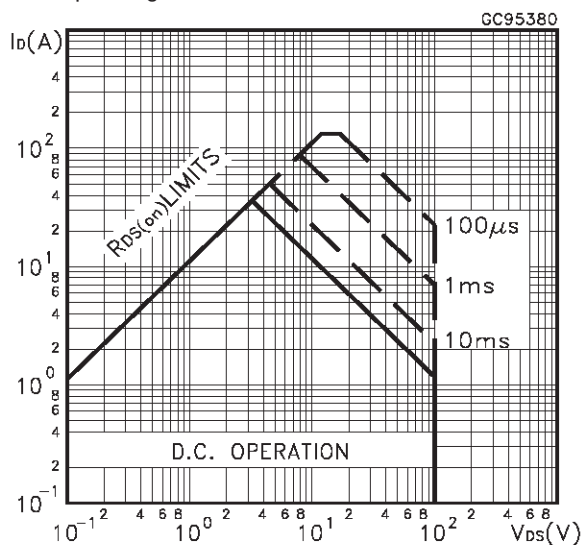
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				35 140	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 30\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 30\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 55\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		110 390 7.5		ns nC A

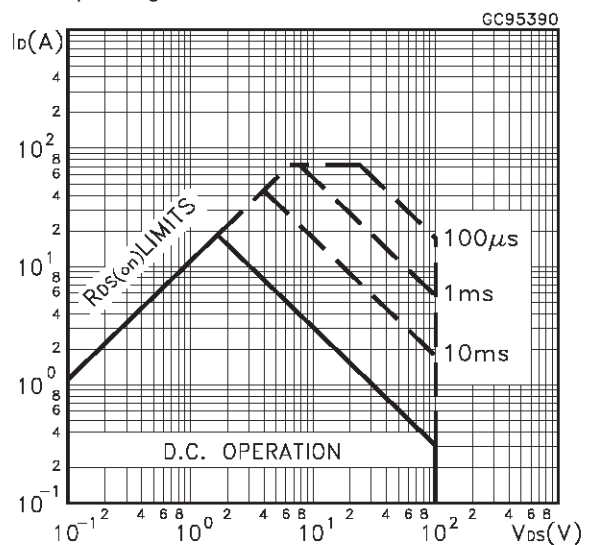
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(\bullet) Pulse width limited by safe operating area.

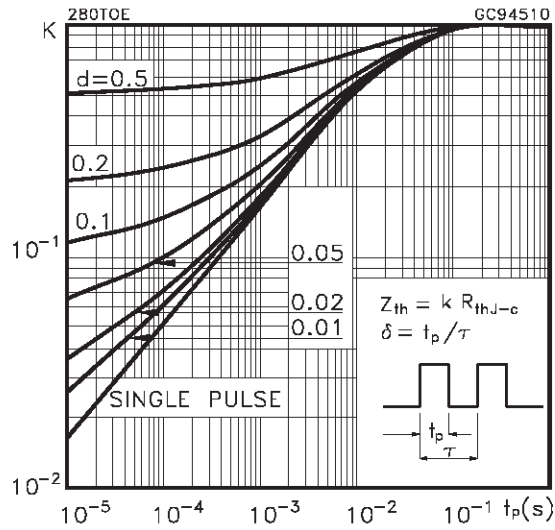
Safe Operating Area for TO-220



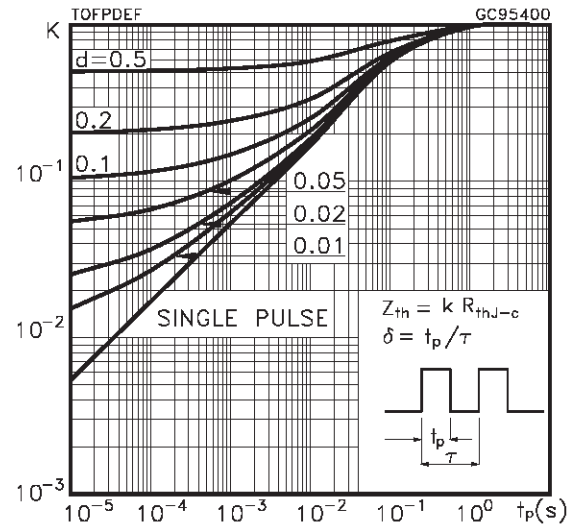
Safe Operating Area for TO-220FP



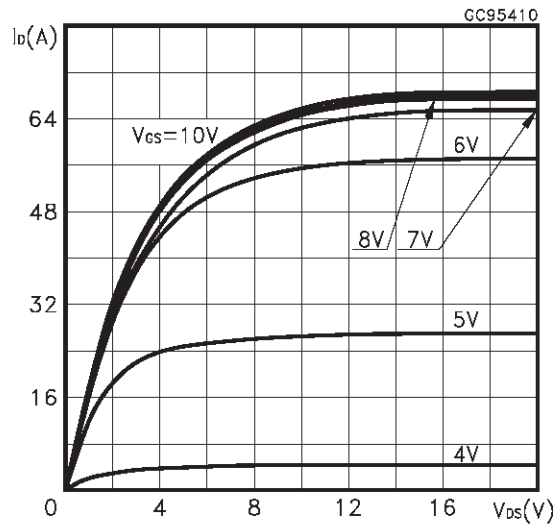
Thermal Impedance



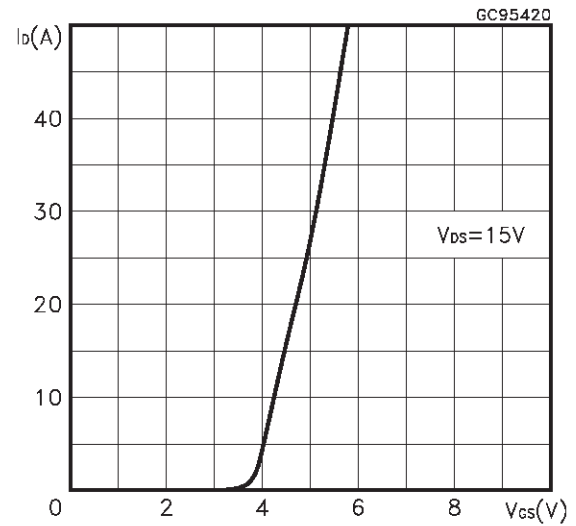
Thermal Impedance for TO-220FP



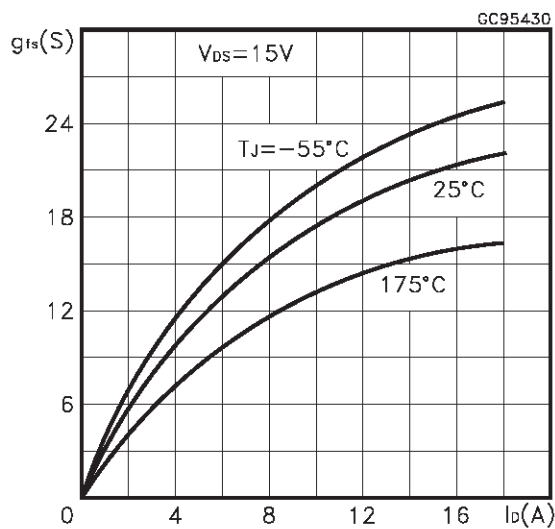
Output Characteristics



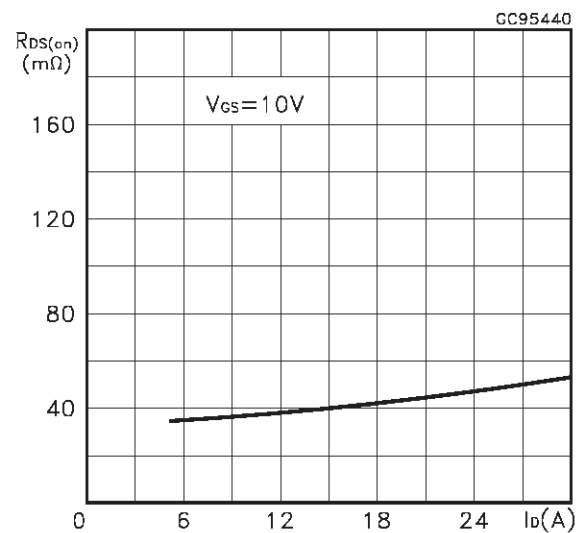
Transfer Characteristics



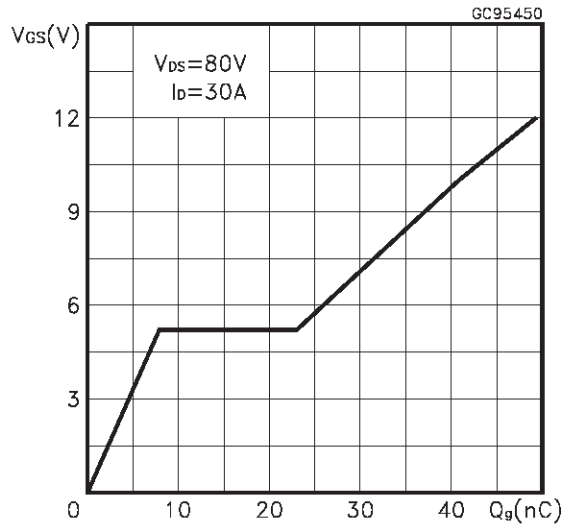
Transconductance



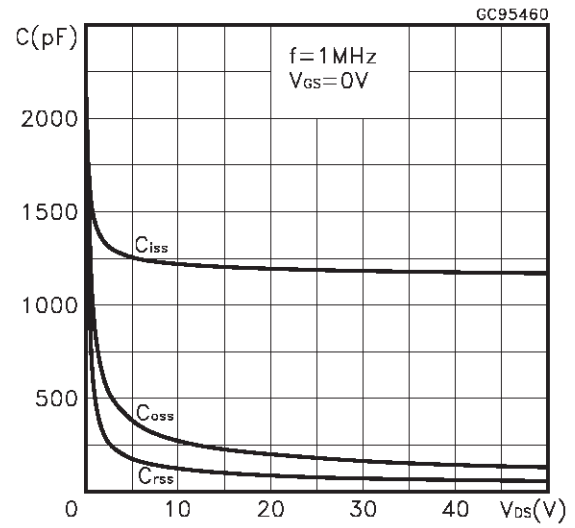
Static Drain-source On Resistance



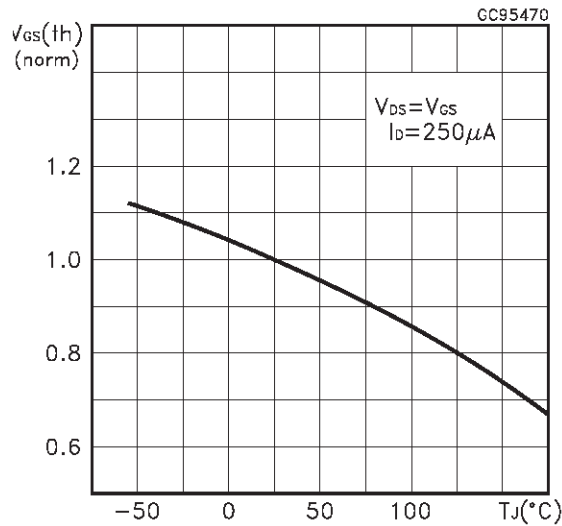
Gate Charge vs Gate-source Voltage



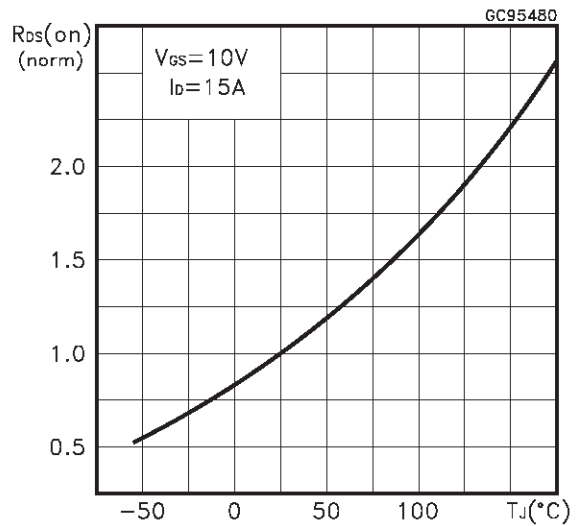
Capacitance Variations



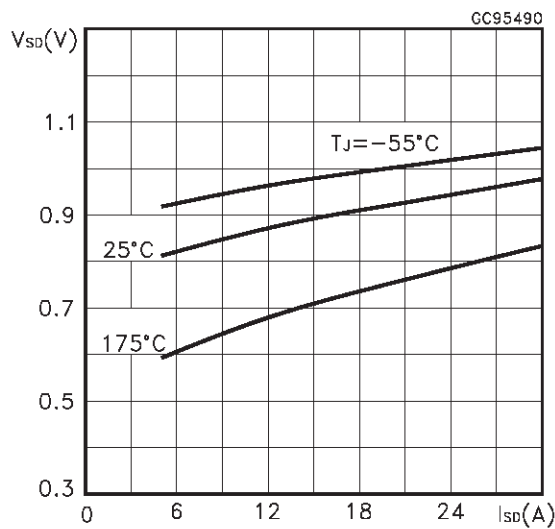
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage Temperature

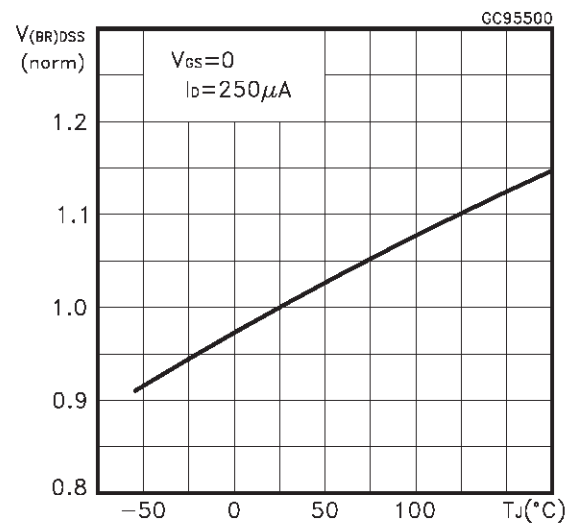


Fig. 1: Unclamped Inductive Load Test Circuit

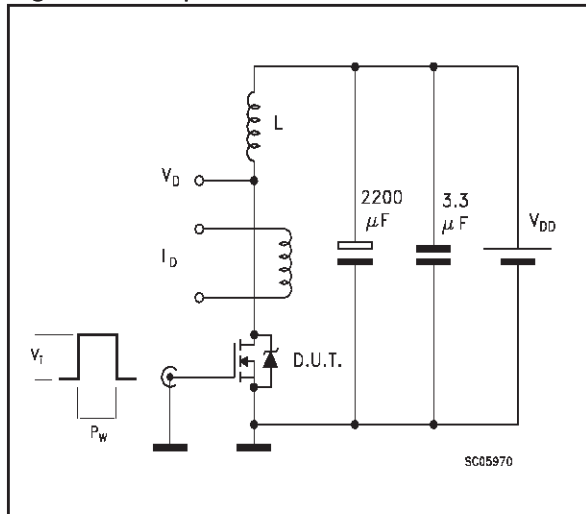


Fig. 2: Unclamped Inductive Waveform

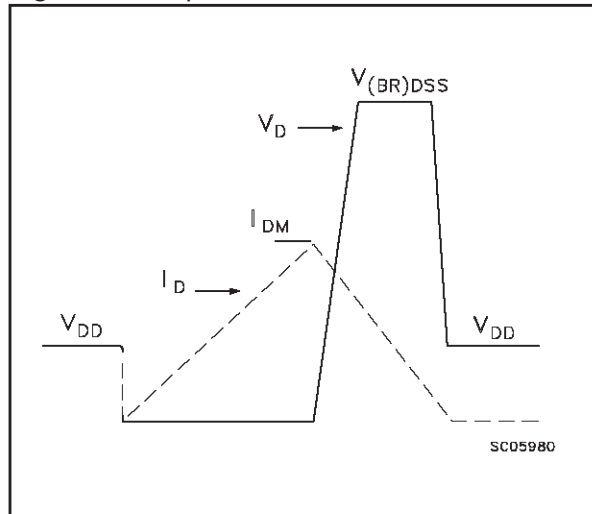


Fig. 3: Switching Times Test Circuits For Resistive Load

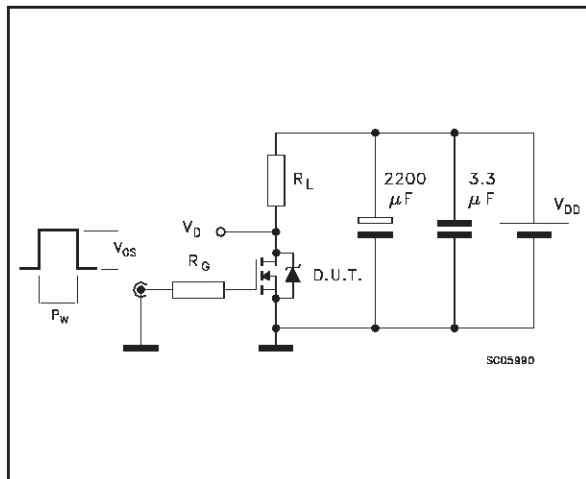


Fig. 4: Gate Charge test Circuit

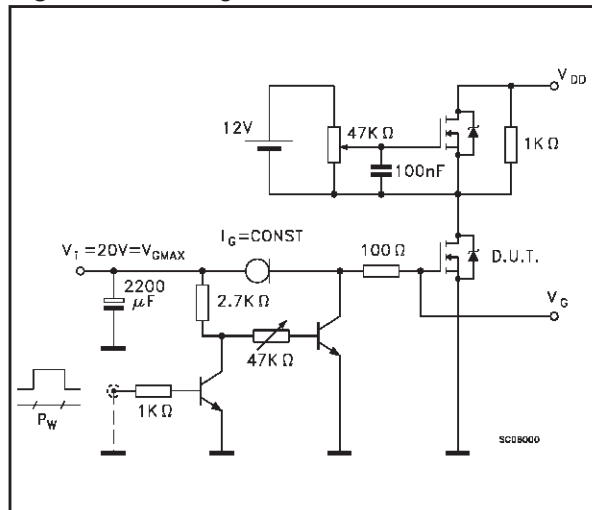
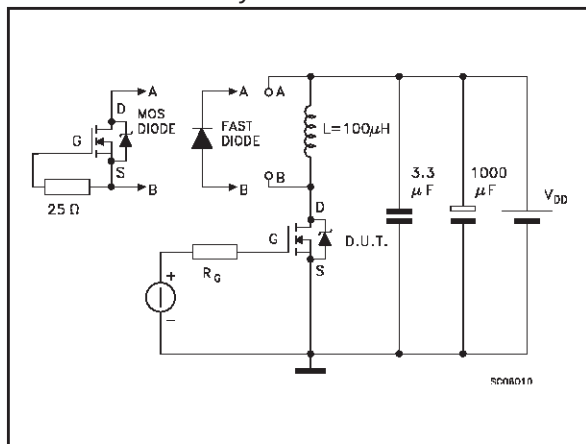
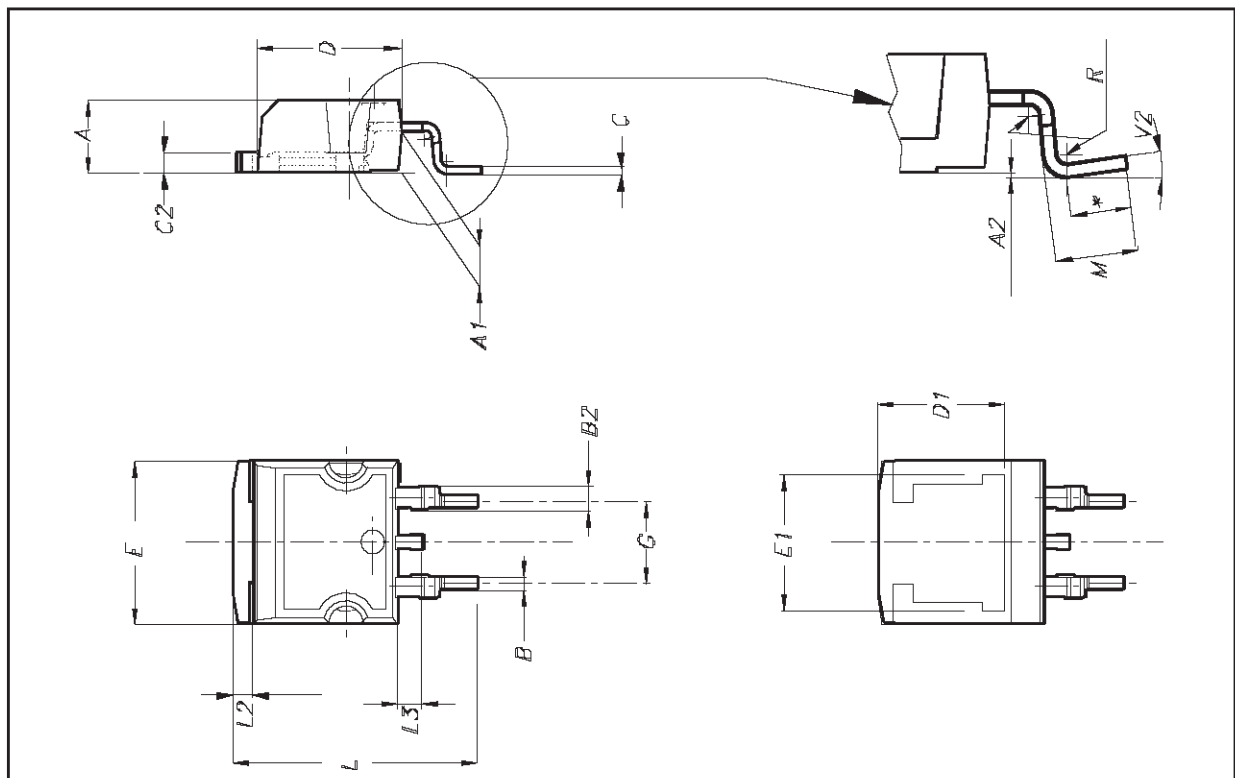


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



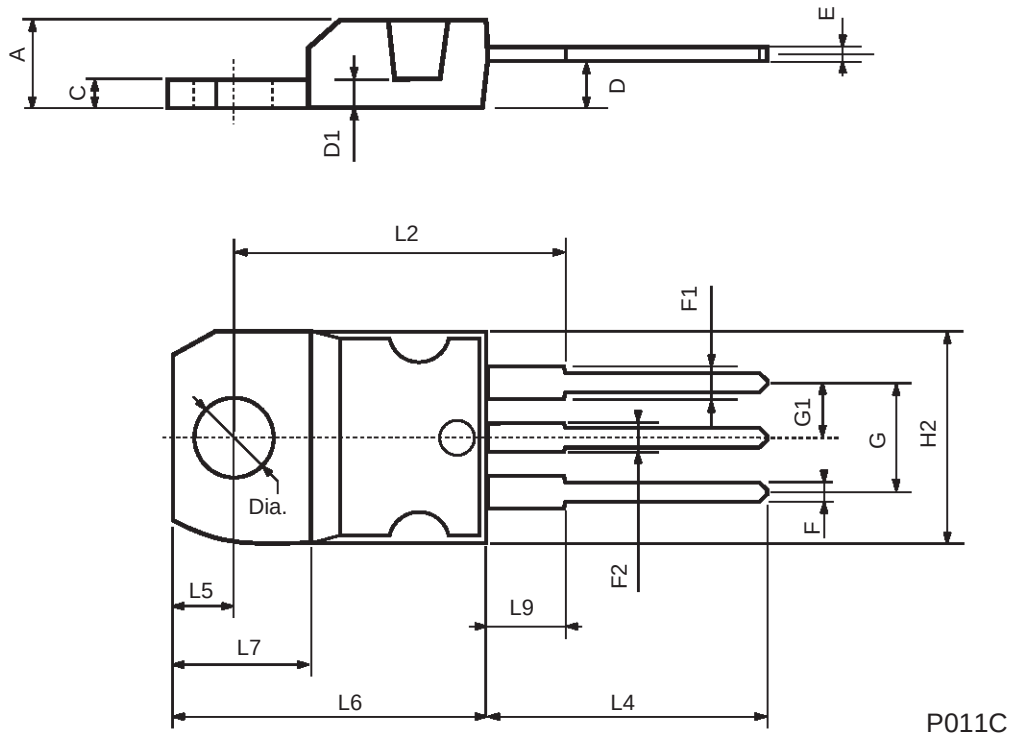
D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°



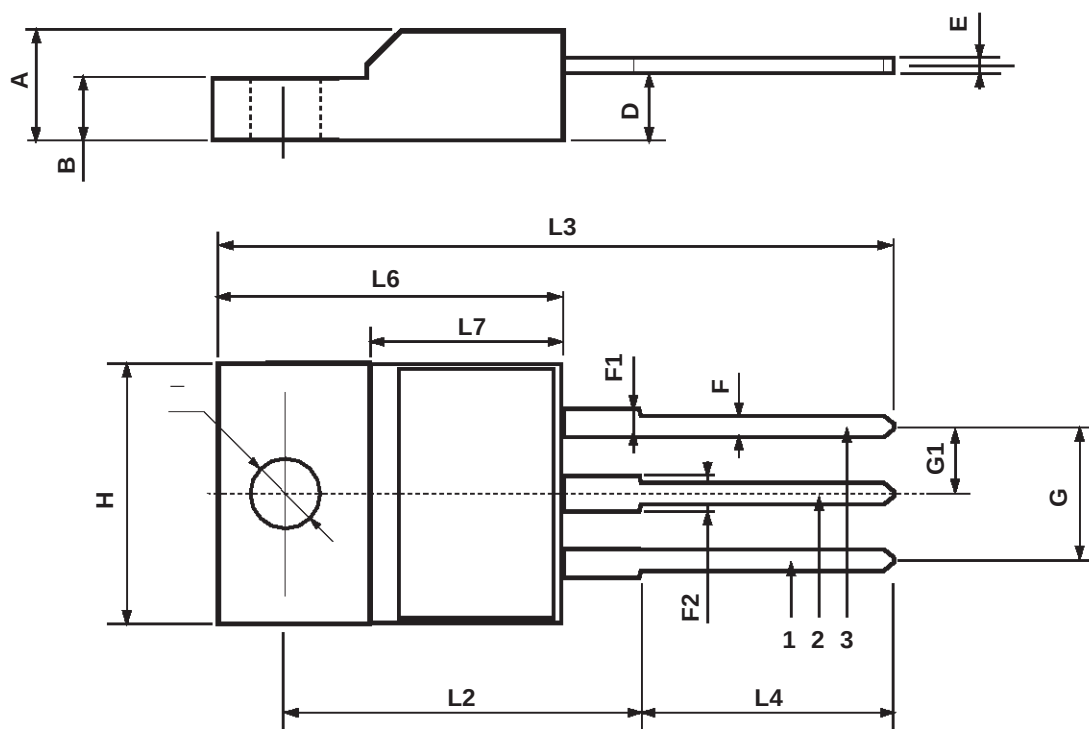
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151

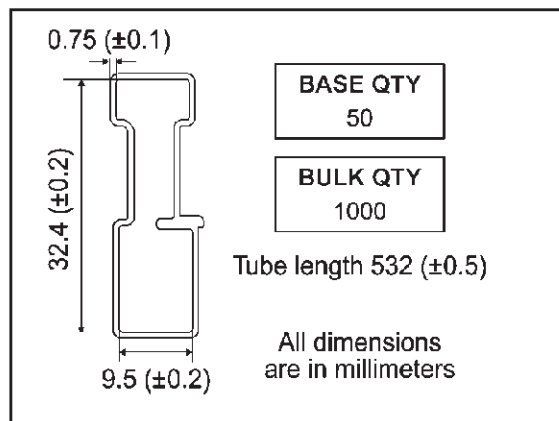


TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



TUBE SHIPMENT (no suffix)*



MENT (suffix "T4")*



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